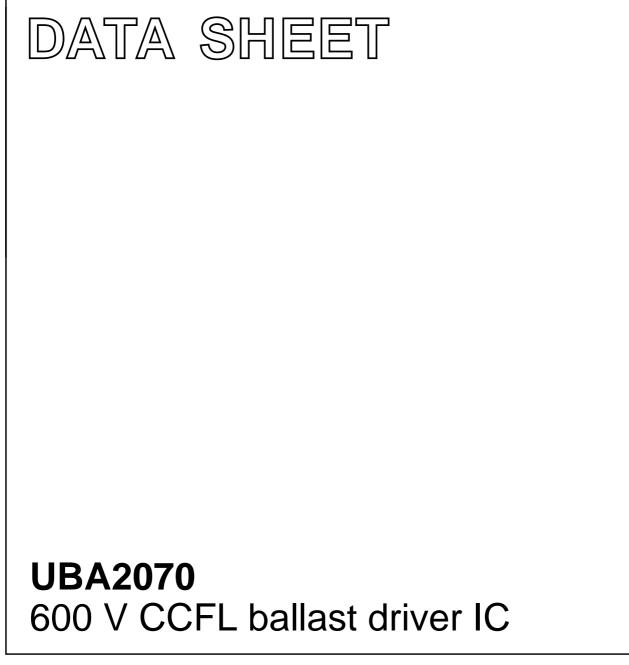
INTEGRATED CIRCUITS



Product specification Supersedes data of 2001 Sep 27 2002 Oct 24



HILIP

UBA2070

FEATURES

- Current controlled operation
- Adaptive non-overlap time control
- Integrated high voltage level shift function
- Power-down function
- Protected against lamp failures or lamp removal
- Capacitive mode protection.

APPLICATION

• The circuit topology enables a broad range of backlight inverters.

ORDERING INFORMATION

GENERAL DESCRIPTION

The UBA2070 is a high voltage integrated circuit for driving electronically ballasted Cold Cathode Fluorescent Lamps (CCFL) at mains voltages up to 277 V (RMS) (nominal value). The circuit is made in a 650 V Bipolar CMOS DMOS (BCD) power logic process. The UBA2070 provides the drive function for the two discrete MOSFETs. Besides the drive function the UBA2070 also includes the level-shift circuit, the oscillator function, a lamp voltage monitor, a current control function, a timer function and protections.

TYPE NUMBER	PACKAGE			
ITFE NUMBER	NAME DESCRIPTION		VERSION	
UBA2070T	SO16	6 plastic small outline package; 16 leads; body width 3.9 mm		
UBA2070P	DIP16	IP16 plastic dual in-line package; 16 leads (300 mil); long body SC		

UBA2070

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITION	MIN.	TYP.	MAX.	UNIT
High voltage	supply		!		1	1
V _{hs}	high side supply voltage	I _{hs} < 30 μA; t < 1 s	-	-	600	V
Start-up stat	te		ł	•	•	
V _{DD(high)}	oscillator start voltage		12.4	13	13.6	V
V _{DD(low)}	oscillator stop voltage		8.6	9.1	9.6	V
I _{DD(start)}	start-up current	V _{DD} < V _{DD(high)}	_	170	200	μA
Reference v	oltage (pin V _{REF})		·			-
V _{ref}	reference voltage	I _L = 10 μA	2.86	2.95	3.04	V
Voltage cont	trolled oscillator			•	·	
f _{bridge(max)}	maximum bridge frequency		90	100	110	kHz
f _{bridge(min)}	minimum bridge frequency		38.9	40.5	42.1	kHz
	ers (pins GH and GL)		•	•		
I _{source}	source current	$V_{GH} - V_{SH} = 0; V_{GL} = 0$	135	180	235	mA
l _{sink}	sink current	V _{GH} – V _{SH} = 13 V; V _{GL} = 13 V	265	300	415	mA
Lamp voltag	e sensor (pin LVS)		ł	•	•	
V _{LVS(fail)}	fail voltage level		1.19	1.25	1.31	V
V _{LVS(max)}	maximum voltage level		1.67	1.76	1.85	V
Average cur	rent sensor (pin CS)					
Voffset	offset voltage	$V_{CS} = 0$ to 2.5 V	-2	0	+2	mV
9 _m	transconductance	f = 1 kHz	100	200	400	μA/mV
Ignition time	er (pin CT)					
V _{OL}	LOW-level output voltage		-	1.4	-	V
V _{OH}	HIGH-level output voltage		_	3.6	_	V

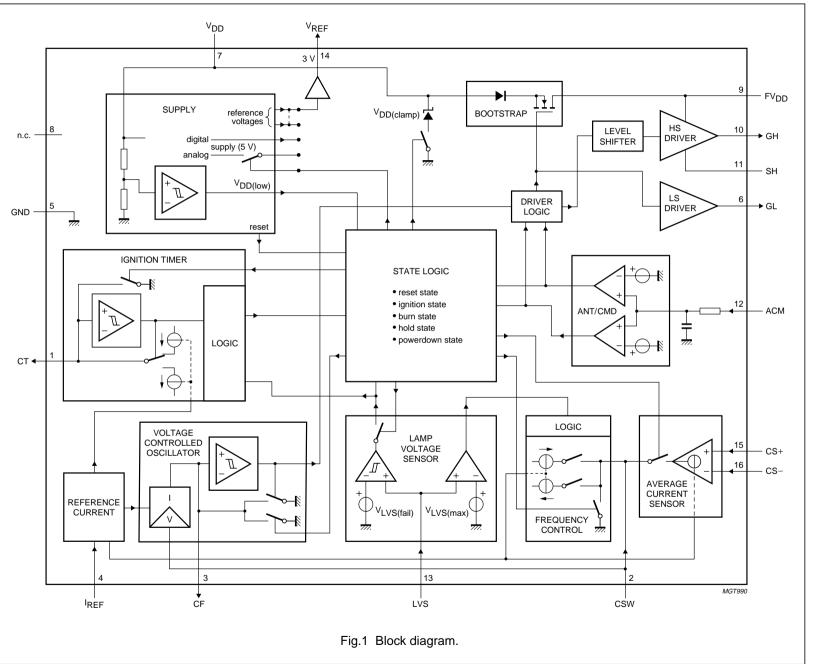


Product specification

600 V CCFL ballast driver IC

UBA2070





4

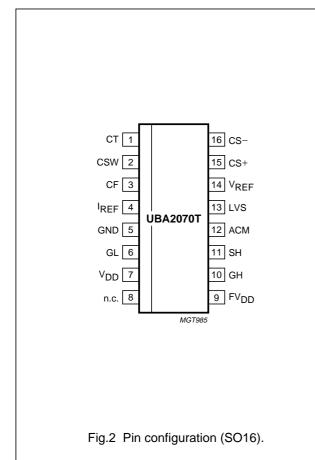
_

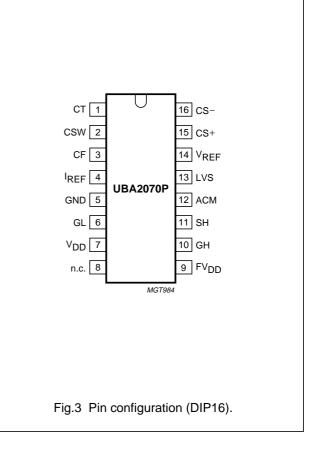
2002 Oct 24

UBA2070

PINNING

SYMBOL	PIN	DESCRIPTION	
СТ	1	ignition timer output	
CSW	2	voltage controlled oscillator input	
CF	3	voltage controlled oscillator output	
I _{REF}	4	internal reference current input	
GND	5	ground	
GL	6	gate of the low side switch output	
V _{DD}	7	low voltage supply	
n.c.	8	not connected	
FV _{DD}	9	floating supply; supply for the high side switch	
GH	10	gate of the high side switch output	
SH	11	source of the high side switch	
ACM	12	capacitive mode input	
LVS	13	lamp voltage sensor input	
V _{REF}	14	reference voltage output	
CS+	15	average current sensor positive input	
CS-	16	average current sensor negative input	





UBA2070

FUNCTIONAL DESCRIPTION

Start-up state

Initial start-up can be achieved by charging C_{VDD} using an external start-up resistor. The start-up of the circuit is such, that the MOSFETs T_{Is} and T_{hs} shall be non-conductive. The circuit will be reset in the start-up state. If the V_{DD} supply reaches the value of $V_{DD(high)}$ the circuit starts oscillating. A DC reset circuit is incorporated in the high side (hs) driver. Below the lockout voltage at pin FV_{DD} the output voltage ($V_{GH} - V_{SH}$) is zero. The voltages at pins CF and CT are zero during the start-up state.

Oscillation

The internal oscillator is a Voltage Controlled Oscillator circuit (VCO) which generates a sawtooth waveform between the high level at pin CF and 0 V (see Fig.4). The frequency of the sawtooth is determined by C_{CF} , R_{IREF} and the voltage at pin CSW. The minimum and maximum frequencies are determined by C_{CF} and R_{IREF} . The minimum to maximum ratio is fixed internally. The sawtooth frequency is twice the half bridge frequency. The IC brings the MOSFETs T_{hs} and T_{ls} alternately into conduction with a duty factor of 50%. The oscillator starts oscillating at f_{max} . During the first switching cycle the MOSFET T_{ls} is switched on. To charge the bootstrap capacitor the first conduction time after the start-up state is made extra long. In all other cases the duty factor at the start is 50%.

Non-overlap time

The non-overlap time is realized with an Adaptive Non-Overlap circuit (ANT). By using this circuit, the application determines the duration of the non-overlap time (determined by the slope of the half bridge voltage and detected by the signal across R_{ACM}) and makes the non-overlap time optimum for each frequency (see Fig.4). The minimum non-overlap time is internally fixed. The maximum non-overlap time is internally fixed at approximately 25% of the bridge period time.

Timing circuit

A timing circuit is included (a clock generator) to determine the maximum ignition time. The ignition time is defined as 1 pulse at pin CT; the lamp has to ignite within the duration of this pulse. The timer circuit starts operating when a critical value of the lamp voltage $[V_{LVS(fail)}]$ is exceeded. When the timer is not operating the capacitor at pin CT is discharged by 1 mA to 0 V.

Ignition state

After the start at f_{max} the frequency will decrease due to charging the capacitor at pin CSW with an internally fixed current. During this continuous decrease in frequency, the circuit approaches the resonant frequency of the lamp. This will cause a high voltage across the lamp, which ignites the lamp. The ignition voltage of the lamp is designed to be above the V_{LVS(fail)} level. If the lamp voltage exceeds this voltage level the ignition timer is started (see Fig.5).

Burn state

If the lamp voltage does not exceed the $V_{LVS(max)}$ level the voltage at pin CSW will continue to increase until the clamp level at pin CSW is reached. As a consequence the frequency will decrease until the minimum frequency is reached. When the frequency reaches its minimum level it is assumed that the lamp has ignited, the circuit will enter the burn state and the Average Current Sensor (ACS) circuit will be enabled (see Fig.5). As soon as the average voltage across R_{sense} (measured at pin CS–) reaches the reference level at pin CS+, the average current sensor circuit will take over the control of the lamp current. The average current through R_{sense} is transferred to a voltage at the voltage controlled oscillator to regulate the frequency and, as a result, the lamp current.

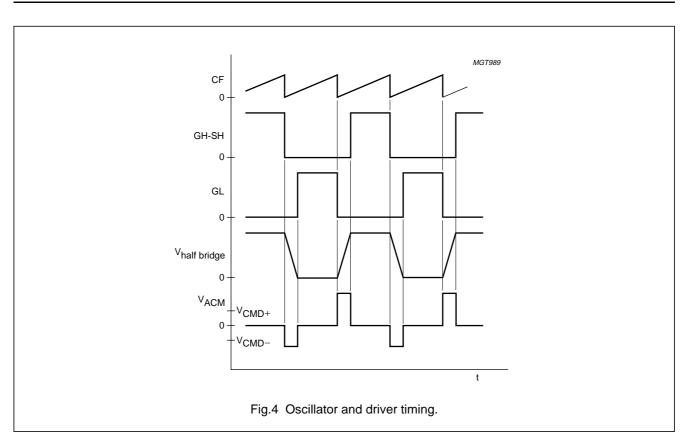
Lamp failure

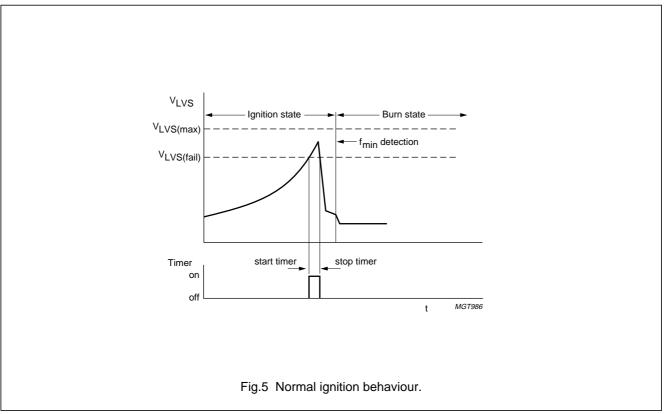
DURING IGNITION STATE

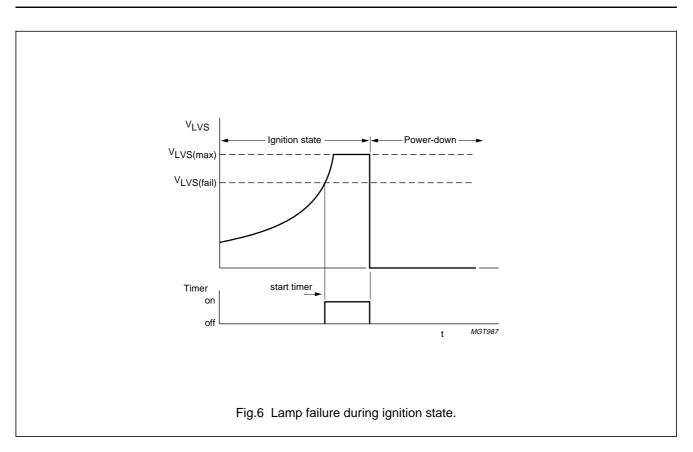
If the lamp fails to ignite, the voltage level increases. When the lamp voltage exceeds the V_{LVS(max)} level, the voltage will be regulated at that level. The ignition timer is started when the V_{LVS(fail)} level is exceeded. If the voltage at pin LVS is above the V_{LVS(fail)} level at the end of the ignition time the circuit stops oscillation and is forced into a Power-down state (see Fig.6). This state is terminated by switching off the V_{DD} supply.

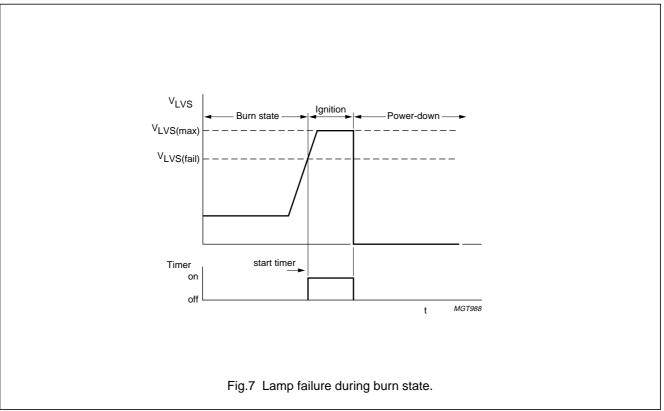
DURING BURN STATE

If the lamp fails during normal operation, the voltage across the lamp will increase and the lamp voltage will exceed the $V_{LVS(fail)}$ level. This forces the circuit to re-enter the ignition state and results in an attempt to re-ignite the lamp. If during restart the lamp still fails, the voltage remains high until the end of the ignition time. At the end of the ignition time the circuit stops oscillating and enters the Power-down state (see Fig.7).









UBA2070

Power-down state

The Power-down state will be entered if, at the end of the ignition time, the voltage at pin LVS is above $V_{LVS(fail)}$. In the Power-down state the oscillation will be stopped and MOSFETs T_{hs} and T_{ls} will be non-conductive. The V_{DD} supply is internally clamped. The circuit is released from the Power-down state by reducing the supply voltage to below $V_{DD(reset)}$.

Capacitive mode protection

The signal across R_{ACM} also gives information about the switching behaviour of the half bridge. If the voltage at R_{ACM} does not exceed the V_{CMD} level during the non-overlap time (see Fig.4), the Capacitive Mode Detection (CMD) circuit assumes that the circuit is in capacitive mode of operation. Consequently the frequency will be directly increased to f_{max} . In this event the frequency behaviour is decoupled from the voltage at pin CSW until the voltage is discharged to zero. An internal filter of 30 ns is included at pin ACM to increase the noise immunity.

Charge coupling

Due to parasitic capacitive coupling to the high voltage circuitry all pins are charged with a repetitive charge injection. Given the typical application the pins I_{REF} and CF are sensitive to this charge injection. For charge coupling of ± 8 pC, a safe functional operation of the IC is guaranteed, independent of the current level.

Charge coupling at current levels below 50 μA will not interfere with the accuracy of the V_{CS} and V_{ACM} levels.

Charge coupling at current levels below 20 μA will not interfere with the accuracy of any parameter.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); all voltages referenced to ground.

SYMBOL	PARAMETER	CONDITION	MIN.	MAX.	UNIT
V _{hs}	high side supply voltage	I _{hs} < 30 μA; t < 1 s	-	600	V
		I _{hs} < 30 μA	-	510	V
V _{ACM}	voltage on pin ACM		-5	+5	V
V _{LVS}	voltage on pin LVS		0	5	V
V _{CS+}	voltage on pin CS+		0	5	V
V _{CS-}	voltage on pin CS-		-0.3	+5	V
V _{CSW}	voltage on pin CSW		0	5	V
T _{amb}	ambient temperature		-25	+80	°C
Tj	junction temperature		-25	+150	°C
T _{stg}	storage temperature		-55	+150	°C
V _{esd}	electrostatic discharge voltage	note 1			
	pins FV _{DD} , GH, SH and V_{DD}		-1000	+1000	V
	pins GL, ACM, CS+, CS–, CSW, LVS, CF, I _{REF} , CT and V _{REF}		-2500	+2500	V

Note

1. In accordance with the human body model: equivalent to discharging a 100 pF capacitor through a 1.5 k Ω series resistor.

UBA2070

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	DESCRIPTION	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient in free air			
	SO16		100	K/W
	DIP16		60	K/W
R _{th(j-t)}	thermal resistance from junction to tie-point			
	SO16		50	K/W
	DIP16		30	K/W

QUALITY SPECIFICATION

In accordance with "SNW-FQ-611D".

CHARACTERISTICS

 V_{DD} = 13 V, $V_{FVDD} - V_{SH}$ = 13 V; T_{amb} = 25 °C; all voltages referenced to ground; see Fig.8; unless otherwise specified.

SYMBOL	PARAMETER	CONDITION	MIN.	TYP.	MAX.	UNIT
High voltage s	upply				-1	1
IL	leakage current on high voltage pins	voltage at pins FV _{DD} , GH and SH = 600 V	-	_	30	μA
Start-up state	(pin V _{DD})					
V _{DD}	supply voltage for defined driver output	$T_{hs} = off; T_{ls} = off$	-	-	6	V
V _{DD(high)}	oscillator start voltage		12.4	13	13.6	V
V _{DD(low)}	oscillator stop voltage		8.6	9.1	9.6	V
V _{DD(hys)}	start-stop hysteresis voltage		3.5	3.9	4.4	V
I _{DD(start)}	start-up current	V _{DD} < V _{DD(high)}	-	170	200	μA
V _{DD(clamp)}	clamp voltage	Power-down mode	10	11	12	V
I _{DD(pd)}	Power-down current	V _{DD} = 9 V	-	170	200	μA
V _{DD(reset})	reset voltage	$T_{hs} = off; T_{ls} = off$	4.5	5.5	7	V
I _{DD}	operating supply current	f _{bridge} = 40 kHz without gate drive	-	1.5	2.2	mA
Reference volt	age (pin V _{REF})	•	•	•		
V _{ref}	reference voltage	I _L = 10 μA	2.86	2.95	3.04	V
I _{ref}	reference current	source	1	-	-	mA
		sink	1	-	-	mA
Zo	output impedance	I _L = 1 mA source	_	3	-	Ω
$\Delta V_{ref} / \Delta T$	temperature coefficient of V _{ref}	I _L = 10 μA; T _{amb} = 25 to 150 °C	-	-0.64	-	%/K
Current supply	/ (pin I _{REF})					
VI	input voltage		-	2.5	-	V
l _l	input current		65	-	95	μA

SYMBOL	PARAMETER	PARAMETER CONDITION		TYP.	MAX.	UNIT
Voltage contro	lled oscillator		l	4		ļ
t _{start}	first output oscillator stroke	after start-up state only	-	50	-	μs
f _{bridge(max)}	maximum bridge frequency		90	100	110	kHz
f _{bridge(min)}	minimum bridge frequency		38.9	40.5	42.1	kHz
Δf _{stab}	frequency stability	$T_{amb} = -20$ to +80 °C	-	1.3	-	%
t _{no(min)}	minimum non-overlap time	GH to GL	0.68	0.90	1.13	μs
		GL to GH	0.75	1	1.25	μs
t _{no(max)}	maximum non-overlap time	at f _{bridge} = 40 kHz; note 1	-	6.7	-	μs
PIN CSW		- •		•	•	
Vi	input voltage		2.7	3	3.3	V
V _{clamp}	clamp voltage	burn state	2.8	3.1	3.4	V
PIN CF	- I		•	•		
I _{start}	start current	V _{CF} = 1.5 V	3.8	4.5	5.2	μA
I _{min}	minimum current	V _{CF} = 1.5 V	-	21	-	μA
I _{max}	maximum current	V _{CF} = 1.5 V	-	54	_	μA
V _{OH}	HIGH-level output voltage	f = f _{min}	-	2.5	-	V
Output drivers	;		-		1	
V _{boot}	bootstrap diode forward drop	l = 5 mA	1.3	1.7	2.1	V
V _{FVDD}	lockout voltage on pin FV _{DD}		2.8	3.5	4.2	V
I _{FVDD}	floating well supply current on pin FV _{DD}	DC level at V _{GH} – V _{SH} = 13 V	-	35	-	μA
PINS GH AND G	L	·	•	•	•	
Isource	source current	$V_{GH} - V_{SH} = 0; V_{GL} = 0$	135	180	235	mA
l _{sink}	sink current	$V_{GH} - V_{SH} = 13 V;$ $V_{GL} = 13 V$	265	300	415	mA
V _{OH}	HIGH-level output voltage	l _o = 10 mA	12.5	-	-	V
V _{OL}	LOW-level output voltage	l _o = 10 mA	-	-	0.5	V
HIGH SIDE AND L	OW SIDE		-	•	•	
R _{on}	on resistance	l _o = 10 mA	32	39	45	Ω
R _{off}	off resistance	l _o = 10 mA	16	21	26	Ω
	overlap timing and capacitive mode	detection (pin ACM)				
li	input current	V _{ACM} = 1.25 V	-	_	1	μA
V _{det}	capacitive mode detection voltage	positive	80	100	120	mV
		negative	-68	-85	-102	mV

UBA2070

SYMBOL	PARAMETER	CONDITION	MIN.	TYP.	MAX.	UNIT
Lamp voltage se	ensor (pin LVS)			1		!
li	input current	V _{LVS} = 1.25 V	-	-	1	μA
V _{LVS(fail)}	fail voltage		1.19	1.25	1.31	V
V _{LVS(fail)(hys)}	fail voltage hysteresis		112	140	168	mV
$\Delta V_{LVS(fail)(hys)} / \Delta T$	temperature coefficient hysteresis		-	0.65	-	mV/K
V _{LVS(max)}	maximum voltage		1.67	1.76	1.85	V
I _{o(sink)}	output sink current	$V_{CSW} = 2 V$	2.8	3.2	3.6	μA
I _{o(source)(ign)}	ignition output source current	$V_{CSW} = 2 V$	9.0	10	11	μA
Average current	sensor (pins CS+ and CS–)		·			
li	input current	V _{CS} = 0 V	-	-	1	μA
Voffset	offset voltage	V _{CS} = 0 to 2.5 V	-2	0	+2	mV
I _{o(source)}	output source current	V _{CSW} = 2.0 V	9.0	10	11	μA
I _{o(sink)}	output sink current	V _{CSW} = 2.0 V	9.0	10	11	μA
9 _m	transconductance	f = 1 kHz	100	200	400	μA/mV
Ignition timer (p	in CT)		ł			
I _o	output current	V _{CT} = 2.5 V	5.5	5.9	6.3	μA
V _{OL}	LOW-level output voltage		_	1.4	-	V
V _{OH}	HIGH-level output voltage		_	3.6	-	V
V _{hys}	output hysteresis		2.05	2.20	2.35	V
t _{ign}	ignition time		_	0.257	-	s

Note

1. The maximum non-overlap time is determined by the level of the CF signal. If this signal exceeds a level of 1.25 V the non-overlap will end. This equals a maximum non-overlap time of 6.7 μs at a bridge frequency of 40 kHz.

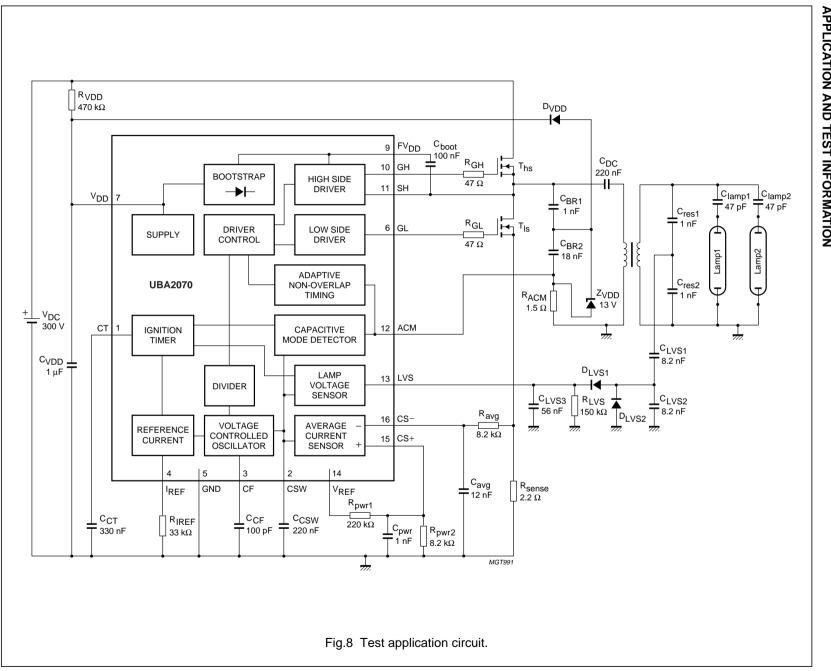


Product specification

600 V CCFL ballast driver IC

UBA2070





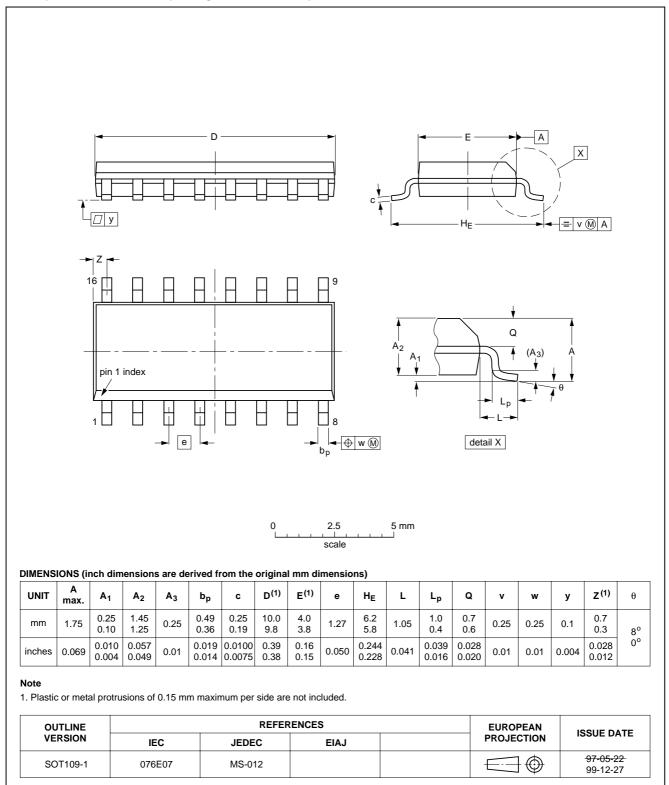
_

UBA2070

600 V CCFL ballast driver IC

PACKAGE OUTLINES

SO16: plastic small outline package; 16 leads; body width 3.9 mm



SOT109-1

DIP16: plastic dual in-line package; 16 leads (300 mil); long body SOT38-1 D M_E seating plane Α2 . A₁ L 0 w @ l≁z е b₁ (e1) 9 M_H 16 pin 1 index Е 8 10 mm 0 5 scale DIMENSIONS (inch dimensions are derived from the original mm dimensions) Z ⁽¹⁾ max. A₂ max. D ⁽¹⁾ E⁽¹⁾ A max A₁ min. UNIT b b₁ с L MF Мн е e₁ w 1.40 0.53 0.32 21.8 6.48 3.9 8.25 9.5 0.51 3.7 7.62 0.254 mm 4.7 2.54 2.2 1.14 0.38 0.23 21.4 6.20 3.4 7.80 8.3 0.055 0.021 0.013 0.86 0.26 0.15 0.32 0.37 inches 0.19 0.020 0.15 0.10 0.30 0.01 0.087 0.045 0.015 0.009 0.84 0.24 0.31 0.33 0.13 Note 1. Plastic or metal protrusions of 0.25 mm maximum per side are not included. REFERENCES OUTLINE EUROPEAN **ISSUE DATE** VERSION PROJECTION IEC JEDEC EIAJ 95-01-19] SOT38-1 050G09 MO-001 SC-503-16 E---99-12-27

UBA2070

SOLDERING

Introduction

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mount components are mixed on one printed-circuit board. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Through-hole mount packages

SOLDERING BY DIPPING OR BY SOLDER WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg(max)}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

MANUAL SOLDERING

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

Surface mount packages

REFLOW SOLDERING

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method. Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

WAVE SOLDERING

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

MANUAL SOLDERING

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

UBA2070

Suitability of IC packages for wave, reflow and dipping soldering methods

MOUNTING	PACKAGE ⁽¹⁾	SOLDERING METHOD			
MOONTING			REFLOW ⁽²⁾	DIPPING	
Through-hole mount	DBS, DIP, HDIP, SDIP, SIL	suitable ⁽³⁾	-	suitable	
Surface mount	BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable	-	
	HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽⁴⁾	suitable	_	
	PLCC ⁽⁵⁾ , SO, SOJ	suitable	suitable	-	
	LQFP, QFP, TQFP	not recommended ⁽⁵⁾⁽⁶⁾	suitable	-	
	SSOP, TSSOP, VSO	not recommended ⁽⁷⁾	suitable	_	

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.
- 4. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 5. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 6. Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 7. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

UBA2070

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products including circuits, standard cells, and/or software described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

UBA2070

NOTES

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2002

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613502/02/pp20

Date of release: 2002 Oct 24

Document order number: 9397 750 10257

SCA74

Let's make things better.





Philips Semiconductors